# **NEMO 3-D USER GUIDE FOR QUANTUM DOT SIMULATIONS**

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#### **INTRODUCTION:**

Nanoelectronics is a fascinating area of research that has significant impact on our lives helping in all sort of problems related to medicine, communications, defense, etc. Due to confinement of carriers in three dimensions, quantum dots (QDs) are ideal candidates for the design of nanoscale optoelectronic devices and quantum information processing. However efficient design of QD based devices is still a huge challenge despite significant advancements in their growth and characterization techniques. This is mainly because QD morphology such as their chemical composition, size, shape etc. significantly changes during the growth of capping layer and the post-growth annealing process. Thus modeling and simulations of QDs with realistic dimensions, atomistic resolution, and essential physical effects such as strain, piezoelectricity etc is critical to understand their electronic and optical properties. This can also provide an efficient way to explore their design space to guide experiments before actual experimentation.

Most of the commercial simulators are based on continuum models and are fundamentally limited to qualitative description of the QD properties. NEMO 3-D, based on fully atomistic strain and electronic structure calculations, is a multi-scale simulator that has been compiled and tested to run on multiple cores of modern age supercomputers. Its capabilities include computation of the electronic structure within an empirical tight-binding model for quantum dots (3-D confinement), nanowires (2-D confinement), quantum wells (1-D confinement), and bulk (no confinement); strain is computed from classical valence force field method. Further details about the simulator can be found at: <a href="https://engineering.purdue.edu/gekcogrp/software-projects/nemo3D/">https://engineering.purdue.edu/gekcogrp/software-projects/nemo3D/</a> and the source code can be downloaded from the NEMO3D distributions group on nanoHUB.org; <a href="https://nanohub.org/groups/nemo3d">https://nanohub.org/groups/nemo3d</a> distribution/.

NEMO 3-D is a large and complex simulator; and understanding of its source code requires considerable knowledge of quantum mechanics, condensed matter theory, and parallel programming. Even for just running a simple QD simulation without knowing its source code, good amount of knowledge about QD modeling, XML files, parallel programming, and Linux/Unix commands is imperative. The inputs to NEMO 3-D executable are specified in an XML based input deck which contains many selectable options to set up execution and output parameters. The purpose of this user guide is to instruct a first time user about basic steps for the compilation of NEMO 3-D source code on a Linux/Unix based machine, setup of an input deck for a simple QD simulation, and understanding of various output files that are generated from a typical QD simulation. It

is advised that a user MUST first become fully familiar and comfortable with the simple example provided in this manual before moving on to a more complex QD device.

## (A) NEMO 3-D Source Code Compilation

Below a step-by-step procedure is presented to download and compile NEMO 3-D code on Linux/Unix based server. As an example, the commands are only presented for a Purdue University machine coates.rcac.purdue.edu. However, this procedure can be used to compile the code at any server machine that has c/c++ language compilers, MPI libraries etc. A user MUST select appropriate compiler in the make.inc file according to the environment where NEMO 3-D is being compiled.

**Step-1:** Downloading the source code from the CVS repository. This part is only for those who have an account on max.ecn.purdue.edu for having an access to the CVS repository. (For an account please contact gekco@purdue.edu)

(a) In your command prompt (assumed \$) type

\$ cvs co NEMO\_3D

After you do this, it will download few license files along with a script file CVS\_nemo3d\_setup.sh. (b) cd to NEMO\_3D folder and run this script file:

- \$ cd NEMO 3D
- \$ ./CVS\_nemo3d\_setup.sh

This command will download all the folders and files from the CVS repository to your local folder.

An alternative way is to download the complete software in the form of a tar file from http://nanoHUB.org svn repository. This can be done by requesting membership on

https://nanohub.org/groups/nemo\_3d\_distribution . After getting the membership, you can download the tar file containing NEMO 3-D source code. Now you can unzip this file:

\$tar -xzvf nemo\_3d\_08\_dec\_2008.tar.gz

#### Step-2: Loading modules

(a) In your command prompt type (on coates.rcac.purdue.edu)

\$ module load mpich2-intel64

A user must load a correct available module here. NEMO 3-D can be compiled on a bunch of different platforms using various modules. Please see the make.inc file for available list of compilers.

Step-3: Building/Making cd to build directory in NEMO\_3D \$ cd build/ Set an environment variable for the XERCESCROOT in NEMO\_3D \$ setenv XERCESCROOT `pwd`/../xerces-c-src2\_1\_0 (You would also find this path at the very end of your downloading all the files n step-1/b.)

\$ vi make.inc go to the list of compiler options and use (on Coates) BUILD\_TYPE = intel9\_32\_mpi\_intelfast Make sure you comment out all other options. Then type, \$ make (This will take some time, about 15-20 minutes, and create the executable in nemo3d/bin directory)

Step-4: Running

cd to nemo3d/bin directory. \$ cd nemo3d/bin You would see that an executable (nemo3d.ex) has been created in the bin directory.

(a) For serial job

Now to run a simple serial job, do the following. Go to the example folder and copy one of the example files to the bin folder. Then give the run command, for example

\$ ./nemo3d.ex example.xml (Next section will explain how to build an XML file).

Outputs will be created in the binary format. To convert to ASCII format do \$ ln -s nemo3d-i386-(press tab key for full name) fmtdat.ex \$ ./fmtdat.ex -a2 example nd Ek

(b) parallel job

To tun a parallel MPI job you should use the pbs system. Here, how we do it on coates at Purdue: \$ cd test \$ qsub Pbs test

Example of Pbs\_test.pbs file is given below.

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Pbs\_test.pbs

#!/bin/tcsh
#PBS -me -l nodes=1:ppn=8,walltime=80:00:00
#PBS -q ncn
#PBS -o nemo.out
#PBS -e nemo.err
# name of the executable goes on next line

set executable="~/NEMO 3D/nemo3d/bin/nemo3d.ex"

##set set PBS\_O\_WORKDIR="~/NEMO\_3D/nemo3d/bin/nemo3d.ex "

cd \$PBS\_O\_WORKDIR

set machinefile=`basename \$PBS\_NODEFILE`

cp \$PBS NODEFILE machinefile.txt

module load mpich2-intel64

mpirun -machinefile machinefile.txt -np 8 \$executable ~/NEMO 3D/nemo3d/bin/example.xml >> live.txt

This pbs script uses 1 node and 8 processors per node. So the code will run on 8 cores of a single cluster node in parallel. The simulation job will be submitted to ncn queue. Output and error log files are nemo.out and nemo.err respectively.

# (B) Setting up an Input Deck

The previous section explains how NEMO 3-D code can be downloaded and compiled to get an executable. NEMO 3-D executable runs on XML based input file, referred to as example.xml in the last section. This XML file is modified by the user to specify device geometry, tight binding material parameters, execution options and output files needed. The executable examines the contents of this file according to predefined syntactical rules. If the file is correctly edited, NEMO 3-D extracts input parameters from this file and executes the code according to the requirements specified in the XML file. The input deck XML is divided into four major parts:

- 1. Geometry Construction
- 2. Material Database
- 3. Execution Parameters
- 4. Output Parameters

Below each part of the XML file will be described in detail. To explain the construction of the input XML file, example device geometry will be used consisting of a single InAs quantum dot in GaAs buffer. The quantum dot is placed on top of a wetting layer 0.5nm thick. The details of the geometry are shown in the figure below.



Figure D.1: An example device geometry consisting of a single InAs quantum dot. The height of the quantum dot is h (nm) and base diameter is d (nm). The strain domain is

marked as Dstrain and electronic structure domain is marked as Delec. The substrate thickness is s (nm) and cap layer is c (nm) thick.

#### (B.1) Geometry Construction

In NEMO 3-D input deck, geometry is constructed by dividing it into various components. For example, the device shown in figure D.1 can be divided into four components: (1) Strain domain (2) Electronic Domain (3) Wetting Layer (4) Quantum dot. Now all of these components will be represented by one shape unit inside the input deck. More important is to know that since the geometry is constructed in NEMO 3-D atomistically, so each subsequent shape replaces the atoms of the previous shape on which this is being placed. For example, let us suppose, we have a box shape of size  $30x30x30nm^3$  made up of GaAs with its bottom left corner at (0, 0, 0). Now we define a second shape of size  $10x10x10nm^3$  starting at (10, 10, 10) coordinate made up of InAs material. The second shape will replace all the 'Ga' atoms with coordinates  $10 \le x \le 20$ ,  $10 \le y \le 20$ , and  $10 \le z \le 20$  by 'In' atoms. This implies that we define the largest shape first, then the next smaller, then the next smaller and so on. Each shape replaces the atoms of the previous shape is previous shape.

In order to fully understand the geometry construction for the input deck of NEMO 3-D, let us construct the geometry defined in figure D.1. The size of various shapes is:

(1) Strain Domain: 30x30x30nm<sup>3</sup>, Shape: Box, Material: GaAs

(2) Wetting Layer: 30x30x30nm<sup>3</sup>, Shape: Box, Material: InAs

(3) Electronic Domain: 20x20x20nm<sup>3</sup>, Shape: Box, Material: GaAs

(4) Quantum Dot: 10x10x4nm<sup>3</sup>, Shape: Dome, Material: InAs

In the input deck, the following shapes will be defined:

**Shape 1**: Box type, GaAs Material, Starting point: (0, 0, 0), Length in x, y, z is: 30, 30, 30 (nm)

 $\rightarrow$  This is the strain domain of the system. Since this is the largest one, we define it as the first shape.

**Shape 2**: Box type, InAs Material, Starting Point: (0, 0, 12.5), Length in x, y, z is: 30, 30, 0.5 (nm)

 $\rightarrow$  This is the wetting layer. Since the wetting layer is grown on the whole substrate, its lateral size is 30nm. The quantum dot will be placed in the middle of the whole structure. The wetting layer z coordinate is calculated as (30-4)/2 = 13nm-0.5nm = 12.5nm

**Shape 3**: Box type, GaAs Material, Starting point: (5, 5, 5), Length in x, y, z is: 20, 20, 20 (nm)

 $\rightarrow$  This is the electronic box. Since the quantum dots are highly confined systems, so we normally choose the smaller region to calculate the electronic structure. This reduces the computational time. Here Shape 1 will be selected for only strain calculations and Shape 3 will be selected for both strain and electronic structure calculations. This shape is also placed in the middle of Shape 1.

**Shape 4**: Box type, InAs Material, Starting Point: (5, 5, 12.5), Length in x, y, z is: 20, 20, 0.5 (nm)

 $\rightarrow$  Since Shape 3 has replaced the wetting layer atoms of Shape 2, we have to redefine the wetting layer inside the electronic domain.

**Shape 5**: Dome type, InAs Material, Starting Point: (10, 10, 13), Length in x, y, z: 10, 10, 4 (nm)

 $\rightarrow$  This is the quantum dot which is placed in the middle of whole structure.

Hence the geometry of a single quantum dot device in figure D.1 can be described in NEMO 3-D input deck with the help of five shapes. Below, I have explained the XML description of each shape component along with a brief description of each of the options. Five such components constitute the whole geometry.



<param type="boolean"> True: This component will be used for local <name>Mark as a subdomain</name> band structure calculations. <cTag>is\_subdomain</cTag> False: This component will not be used for <desc>mark this for future use by local local band structure calculations. bandstructure calculation</desc> This input can be used to select the shapes <value>false</value> that will be part of local band structure </param> calculations. <param type="boolean"> <name>Modify species</name> <cTag>modify\_species</cTag> <desc>modify species within this shape as This option must be kept true to specify described below</desc> materials of the shapes. <value>true</value> </param> <param type="array\_string This option defines the atomic species in the <name>Mat</name> component. For example, if the shape is <cTag>mat</cTag> GaAs material, then it will be {Ga As}. If the <desc>list of atom species</desc> shape is InGaAs material, then it will be {In Ga <value>{ Ga As }</value> As}. </param> This option defines the fraction of a material <param type="array\_real"> <name>Mol</name> in the shape. For example, if the material is InAs or GaAs, then the values will be {1.0 1.0} <cTag>mol</cTag> because both In and As in InAs unit cell will <desc>concentrations of atom species</desc> have equal mol fraction. However, for <value>{ 1.0 1.0 }</value> In0.7Ga0.3As material, the values will be {0.7 </param> <param type="array integer" 0.3 1.0}. <name>Pol</name> This option is used to identify anion and <cTag>pol</cTag> cations in the material defined in the <desc>polarity</desc> above option. 1 -> cation and -1 -> anion. <value>{ 1 -1 }</value> For an alloy such as InGaAs, the value for </param> this option will be {1 1 -1} because In and <param type="option"> Ga are cations and As is anion. <name>Alloy Treatment</name> <cTag>AlloyTreatment</cTag> <desc>algorithm for distributing atoms</desc> This option is only used for alloy materials. It specifies whether the alloy will have <value>RandomInUnitCell</value> a virtual crystal approximation distribu-<option>VCA</option> <option>RandomInUnitCell</option> tion or a random distribution of atoms <option>RandomUnitCells</option> with in the unit cell. If random distribution <option>RandomCluster</option> is selected, each atom type is determined </param> <param type="boolean"> on the basis of a random number generated with in the source code. <name>Fixed Concentration?</name> <cTag>AlloyFixConcentration</cTag> This option when false allows VCA or random <desc>specify alloy concentration with number distribution of alloys as specified above. absolute certainty</desc> <value>false</value> /param> (param type="integer"> This option is only used for alloy materials. It <name>Alloy Cluster Radius</name> specifies the radius of atomic clusters in the <cTag>AlloyClusterRadius</cTag> <desc>radius of clustering in alloys</desc> alloys. <value>1</value> </param> <param type="integer"> <name>Internal variable 1</name> This option is used to find the material. The <cTag>matid3d</cTag> user does not have to change the value of <desc>You should not be seeing this.</desc> this option. Keep it equal to -1. <value>-1</value> </param> </group>

Besides describing the geometry of the device, we have to select some parameters related to entire simulation domain. These parameters define the crystal structure to be constructed, the tight binding parameters to be used etc. Brief description of these options is presented below:



#### (B.2) Material Database

This part of the input deck XML file is the material database. Here, tight binding and strain parameters of various materials are specified. Each material starts with:

<group type="obj">

<name>material\_1</name>  $\rightarrow$  This is the material number in the data base

<cTag>Material</cTag>  $\rightarrow$  This is the tag for the source code to read this option.

<desc>GaAs bulk properties (spds\*)</desc>  $\rightarrow$ The name of the material and
parameter type.

There are currently nineteen (19) materials described in the database. The user does not need to change anything in this section unless new materials need to be specified. A new material can be added by duplicating a material group with resetting material parameters.

#### **(B.3)** Execution Parameters

After specifying the geometry and adding the required materials into the material data base, the next step is to select execution options from the execution parameter set. NEMO 3-D is a huge software package and it allows computation of many different parameters under different settings. For example, we can turn off or on the strain calculation. We can turn on or off the electronic structure calculations. We can turn on or off optical matrix element calculations etc. The flexibility to turn ON/OFF various parameters means that we can reduce the computation time by selecting only those parameters that are needed in a particular study.

The execution parameters that are needed to be selected are described below. There are other parameters that have not been described below but are accessible. These parameters are not important for quantum dot simulations and hence should be left with their default values.



NEMO 3-D allows the application of external electrical and magnetic fields for the study of quantum confined stark shifts and g-factor engineering. Below, the execution parameters related to the application of external electrical or magnetic fields are described:





Typical quantum dot simulation contains millions of atoms. The corresponding single particle Hamiltonians are also very large. The calculation of Eigen-values and Eigen-vectors of these large Hamiltonians poses a very computationally expensive problem. NEMO 3-D have various Eigen-solvers that are optimized to run on many cores to quickly find the Eigen-values and Eigen-vectors to these multi-million atom Hamiltonians. Below I have described the settings of only one Eigen-solver "Lanczos" which is more commonly used for quantum dot simulations. The settings of other Eigensolvers are more or less similar and can be easily adjusted.

<group type="struct"> <name>Algorithms</name> <cTag>ElAlg</cTag> <desc>parameters relating to particular algorithms</desc> <param type="option"> <name>Electronic eigensolver</name> <cTag>ResFind</cTag> <desc>method to find resonances</desc> <value>Lancz</value> <option>Lancz</option> <option>Rayleigh</option> <option>LanczAndRayleigh</option> <option>Direct</option> <option>Readstates</option> <option>ParpackSolver</option> <option>PQTraceminSolver</option> <option>PCTraceminSolver</option> <option>BlockLanczos</option> </param> > param type="integer"> <name>Number of BZ points</name> <cTag>Nk</cTag> <desc>Number of k space points</desc> <value>1</value> </param> <param type="array real"> <name>Initial k-vector</name> <cTag>k0</cTag> the following: <desc>(kx, ky, kz)</desc> <value>{000}</value> </param> <param type="array\_real"> <name>Final k-vector</name> <cTag>kf</cTag> <desc>(kx, ky, kz)</desc> <value>{ 0 0 0 }</value> </param>

Here we can select the eigen-solver to calculate eigen-values of the single particle Hamiltonain. Various eigensolvers are part of the NEMO 3-D package and can be selected for accuracy and speed requirements. For new users, it is recommended to use the Direct solver for bulk band structure calculations and the Lanczos (Lancz) solver for quantum dot energy spectrum calculation.

Here we specify the k-space parameters to calculate the energy spectrum. Number of Bz points specify how many points will be calculated within one brillioun zone. Initial and final k-space points describe the direction in the k-space to calculate the energy spectrum. For example to calculate the bulk band structure of GaAs material in the [111] direction, one can specify Number of BZ points: 60 initial k-vector: {0 0 0} final k-vector: {1 1 1} The default value is for an InAs guantum dot system, where the material is a direct band gap material so we calculate eigen-values at the (0 0 0) point of k-space.



Below the selection of strain parameters is described. Strain is calculated in NEMO 3-D by relaxing the atoms according to the valence force field method by minimizing the total energy of the system. The selection of the correct strain model and the boundary conditions is critical for proper strain calculations:







#### (B.4) Output Parameters

The final section of the NEMO 3-D input deck is the output parameter section. After selecting the right parameters in the execution parameter section, the NEMO 3-D simulation will compute the various physical quantities for a quantum dot simulation. However, in general, all of the computed quantities are not needed. For example, one might need the electronic structure including the strain and external electrical field, but not the strain data or electrical field data. The solution will be to turn ON the strain, external field and electronic structure calculations in the execution parameters section and turn OFF the strain and external field in the output parameter section. The electronic structure will be turned ON in the output parameter section. These settings will generate output files which contain the electronic structure data including the strain and the external fields. Since the quantum dot simulations are multi-million atom simulations, so the output files will be very large. By turning OFF the unnecessary output files in the output parameter section, much of the disk space can be saved.

Below, the various options available in the output parameter section of the NEMO 3-D input deck are described:





### (C) Format of Output Files Generated by NEMO 3-D

After compiling NEMO 3-D source code to obtain an executable and setting up the input deck XML file for the device geometry construction, the simulation can be run serially on a single processor or as a parallel job or various processors using a pbs script as defined in section A. If the job completes successfully, the working directory will contain the output files that were selected in the output parameter section. Below, the name and format of various output files are presented for the first time user to understand the output generated by NEMO 3-D simulations. In general, the output files generated by NEMO 3-D have the name of XML file as their prefix. For example, if the name of input deck is example.xml, then all of the output files will have name example.nd\_\*.

(1) Energy Dispersion: The name of this file is \*Ek. This file contains E versus k values. The format is:

<kx ky kz Energy>

(2) Eigen-vectors: For each Eigen-value (energy level), one Eigen-vector file is computed. For example, if \*Ek file contains 10 energy levels, then there will be 10 Eigen-vector files corresponding to each energy level. The name of the files will be \*evec\_*i*, where *i* is the index number of the energy level to which this Eigen-vector belong. The format of the file is:

<real complex>  $\rightarrow$  real and complex parts of Eigen-vector.

(3) Wave functions: For each Eigen-value (energy level), one wave function file is computed. For example, if \*Ek file contains 10 energy levels, then there will be 10 wave function files corresponding to each energy level. The name of the files will be \*wf\_*i*, where *i* is the index number of the energy level to which this wave function belong. The format of the file is:  $< |\psi|^2 >$ 

(4) Local Band Structure: Local band structure file contains local band edge data in the sub domain specified in the execution parameter section. One file is generated for each processor. The name of file is: \*Ek\_proc\_pn\_kx0.000\_ky\_0.000\_kz\_0.000\_r where pn is the processor number. The format of the file is:

<kx ky kz x y z energy atomType>

- (5) Trace of Eigen-values: The name of file is \*eval. The file contains Eigen-value versus iteration number of the Lanczos Eigen-solver. The format of the file is: <Iteration number Eigen-value>
- (6) Optical Matrix Element: The output files generated are optical transition rates for incident light polarization along the X, Y and Z Cartesian coordinates. The file names are \*TransX, \*TransY, and \*TransZ. The format of the files is:

<energy\_state\_i energy\_state\_f energy\_gap transition\_rate>

(7) Atom Position Files: Atom position file before the strain contains atom coordinates in the Cartesian real space. The name of the file is \*rAtom\_0. The atom positions file after the strain contains coordinates in the Cartesian real space after strain relaxation. The name of this file is \*rAtom\_1. The format of both files is:

<x y z>

(8) Atom Type File: This file contains the type of each atom in the form of a unique ASCII number assigned to the atom. For example, In atom is assigned a number 14, As atom is assigned a number 12, Ga atom is assigned a number 10 etc. The name of the file is \*aType and format of the file is:

<atom\_type>

(9) Neighbor Index File: The name of the file is \*nbrIndx. This file contains information of 4 nearest neighbors for each atom in the geometry. The ordering is the same as the ordering of the atom positions in the rAtom file. The format of this file is: <neighbor-1 neighbor\_2 neighbor\_3 neighbor\_4>

**Note:** This document is created to serve as a guide for first time users of NEMO 3-D software who intend to use it for quantum dot simulations. The manual is created with great care to provide accurate information. However, the authors do not take any responsibility of any kind for the contents presented. The entire risk as to the quality, the performance, and the fitness of the manual for any particular purpose lies with the party using it. In no event will the authors or any party who distributed the manual be liable for damages or for any claim(s) by any third party, including but not limited to, any lost profits, lost monies, lost data or data rendered inaccurate, losses sustained by third parties, or any other special, incidental or consequential damages arising out of the use or inability to use the program, even if the possibility of such damages has been advised against.